Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Extended temperature range T_i = 175 °C
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM (class H2)
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V_{GS}	gate-source voltage]		-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	2.5	Α
Static charac	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 2.5 \text{ A}; T_j = 25 \text{ °C}$		-	96	123	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	<u> </u>	D
2	D	drain		
3	G	gate	0 	G ★ \
4	S	source	TSOP6 (SOT457)	\ \\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
5	D	drain		
6	D	drain		s
				017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMN120ENEA	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMN120ENEA	J5

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	2.5	А
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	1.8	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	10	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	670	mW
			[1]	-	1.7	W
		T _{sp} = 25 °C		-	7.5	W
Tj	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source-drain d	iode		'		•	
Is	source current	T _{amb} = 25 °C	[1]	-	1.7	Α
ESD maximum	rating		'		•	
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V
Avalanche ruge	gedness		,	'		
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	T _{j(init)} = 25 °C; I _D = 0.3 A; DUT in avalanche (unclamped)		-	9	mJ

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain $6 \, \mathrm{cm}^2$.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

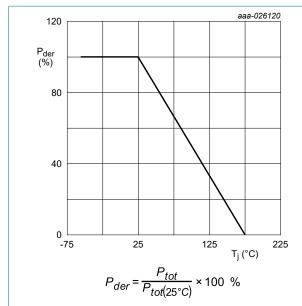


Fig. 1. Normalized total power dissipation as a function of junction temperature

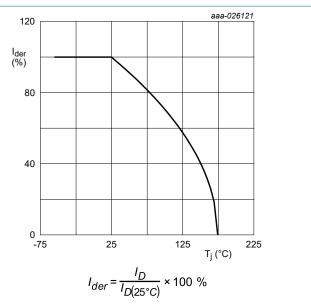


Fig. 2. Normalized continuous drain current as a function of junction temperature

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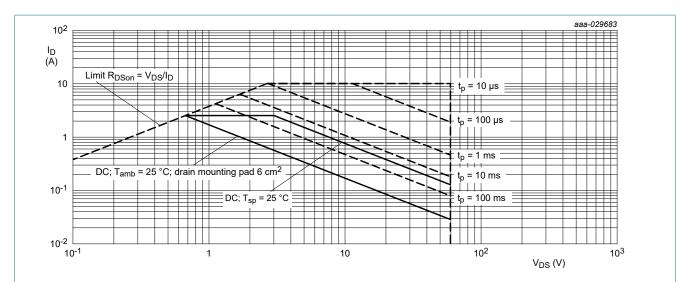


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

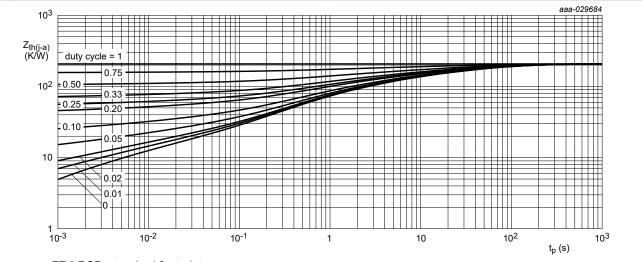
60 V, N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

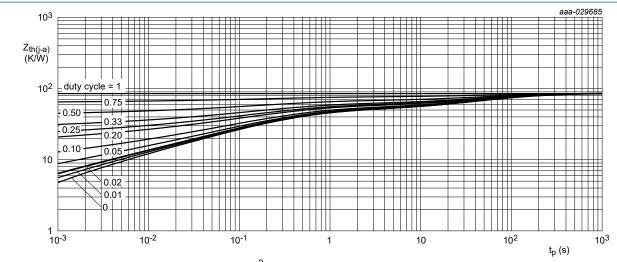
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	195	225	K/W
junction to ambient	junction to ambient		[2]	-	78	90	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	15	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

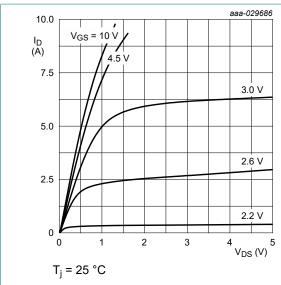
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10. Characteristics

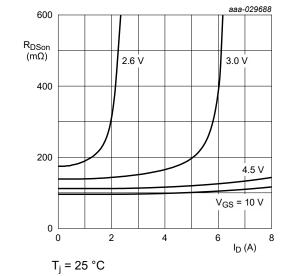
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \degree C$	1.3	1.7	2.7	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 2.5 A; T _j = 25 °C	-	96	123	mΩ
	resistance	V _{GS} = 10 V; I _D = 2.5 A; T _j = 175 °C	-	208	267	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 2.3 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	108	146	mΩ
g _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 2 \text{ A}; T_j = 25 \text{ °C}$	-	8.5	-	S
R_G	gate resistance	f = 1 MHz; T _j = 25 °C	-	11	-	Ω
Dynamic ch	naracteristics					
$Q_{G(tot)}$	total gate charge	$V_{DS} = 30 \text{ V}; I_D = 2.5 \text{ A}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}$	-	4	6	nC
Q _{GS}	gate-source charge	V _{DS} = 30 V; I _D = 2.5 mA; V _{GS} = 10 V;	-	0.5	-	nC
Q_{GD}	gate-drain charge	T _j = 25 °C	-	0.9	-	nC
C _{iss}	input capacitance	V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V;	-	196	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	24	-	pF
C _{rss}	reverse transfer capacitance		-	15	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; I_D = 2.5 \text{ A}; V_{GS} = 10 \text{ V};$	-	3	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	6	-	ns
t _{d(off)}	turn-off delay time]	-	8	-	ns
t _f	fall time	1	-	3	-	ns
Source-dra	in diode		'			,
V _{SD}	source-drain voltage	I _S = 1.7 A; V _{GS} = 0 V; T _j = 25 °C	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 0.8 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	11	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	4	-	nC

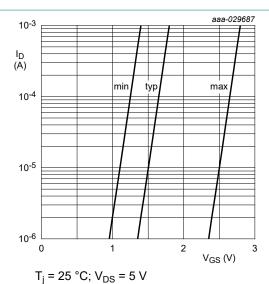
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Output characteristics: drain current as a function of drain-source voltage; typical values



Drain-source on-state resistance as a function Fig. 8. of drain current; typical values



Sub-threshold drain current as a function of Fig. 7. gate-source voltage

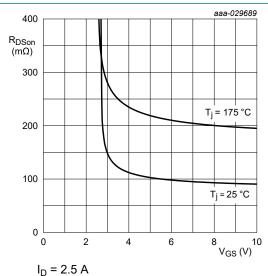


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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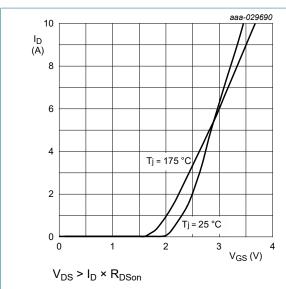


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

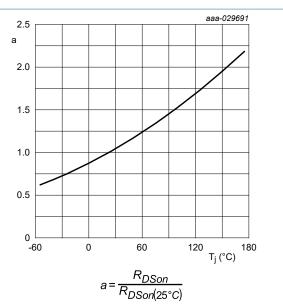


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

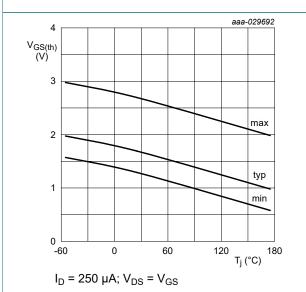


Fig. 12. Gate-source threshold voltage as a function of junction temperature

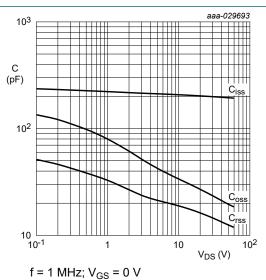


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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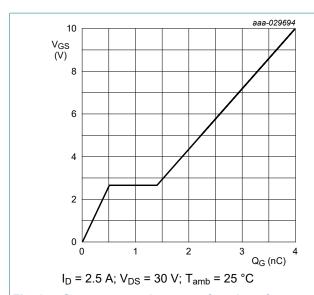


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

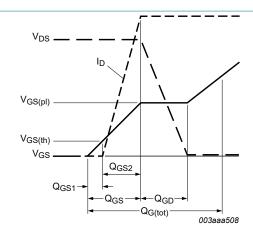


Fig. 15. Gate charge waveform definitions

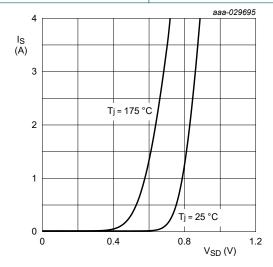
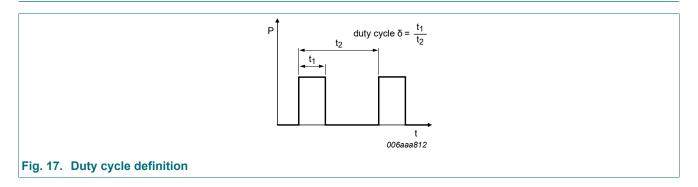


Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

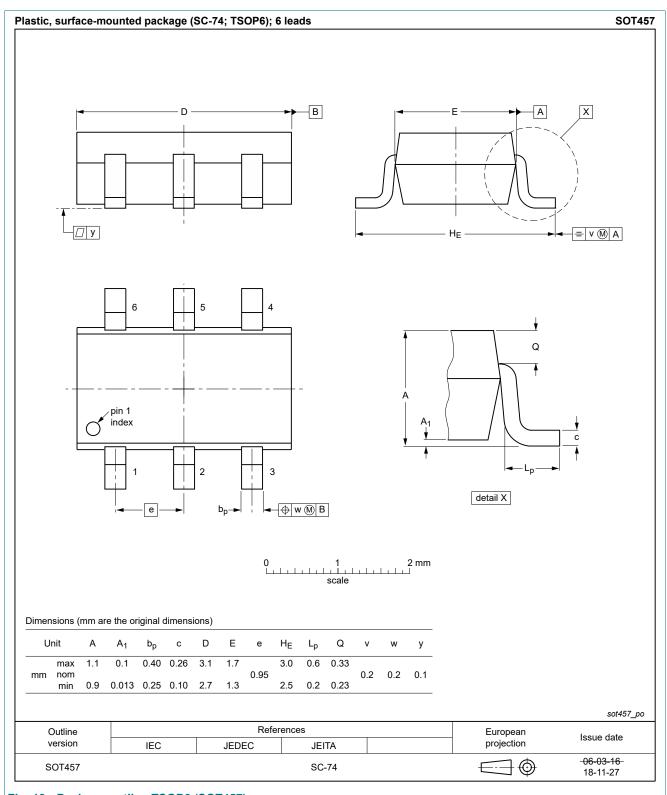
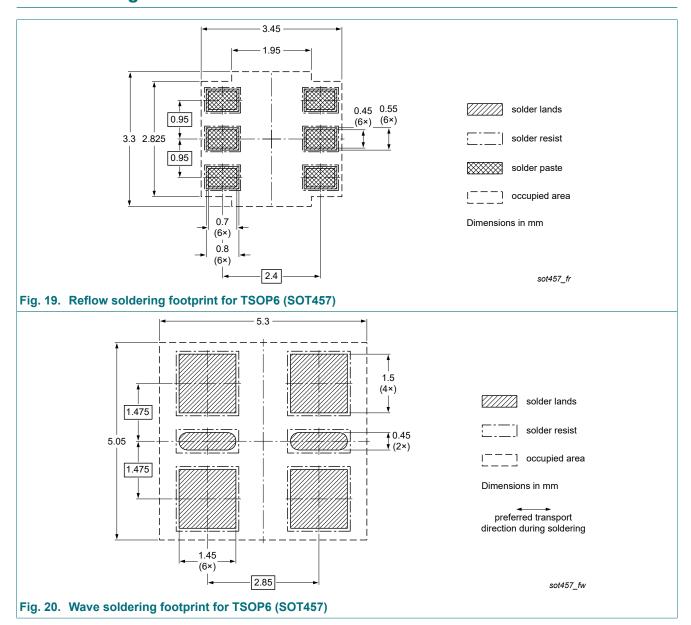


Fig. 18. Package outline TSOP6 (SOT457)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN120ENEA v.1	20190429	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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